



# FAN7387V Ballast Control IC for Compact Fluorescent Lamp

#### **Features**

- Integrated Half-Bridge MOSFET
- Internal Clock Using RCT
- Enable External Sync Function Using RCT
- Dead-Time Control by using Resistor
- Shut Down (Disable Mode)
- Internal Shunt Regulator
- UVLO Function High and Low Side

#### **Applications**

Compact Fluorescent Lamp Ballast

#### **Description**

The FAN7387V, developed using Fairchild's unique high-voltage process and system-in-package (SiP) concept, is a ballast-control integrated circuit (IC) for a compact fluorescent lamp (CFL). The FAN7387V has a simple oscillating circuit using an external resistor and capacitor so the frequency variation is stable across the temperature range. FAN7387V has a external pin for dead time control and shutdown. By using this resistor, a designer can choose the optimum dead time to reduce the power loss on internal switching devices (MOSFETs).

8-DIP



#### **Ordering Information**

Part Number	Operating Temperature	© Eco Status	Package	Packing Method
FAN7387VN	-40 to +125°C	RoHS	8-Lead, Dual-In-line Package (DIP)	Tube



#### **Typical Applications Diagrams**

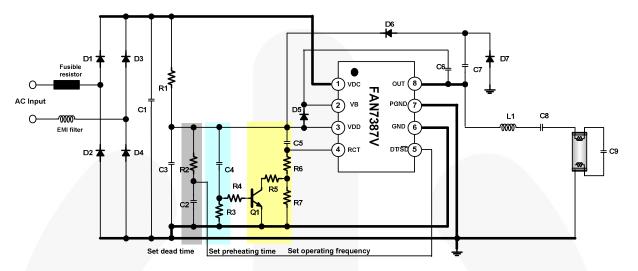


Figure 1. Typical Application Circuit for Fluorescent Lamp (Rapid Starting Method without PTC)

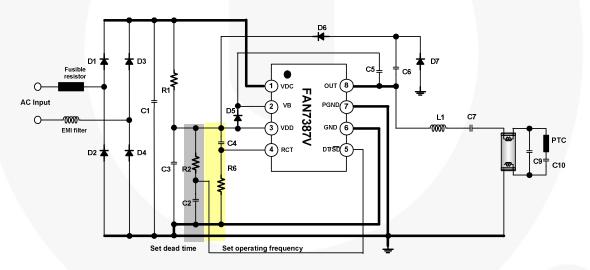


Figure 2. Typical Application Circuit for Fluorescent Lamp (Rapid Starting Method with PTC)

#### **Internal Block Diagram**

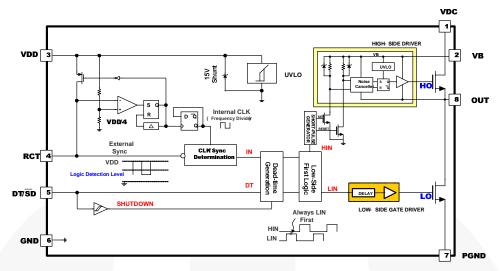


Figure 3. Functional Block Diagram

## **Pin Configuration**

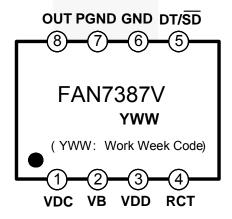


Figure 4. Pin Configurations (Top View)

#### **Pin Definitions**

Pin#	Name	Description
1	VDC	High-voltage Supply
2	VB	High-Side Floating Supply
3	VDD	Supply Voltage
4	RCT	Oscillator Frequency Set Resistor and Capacitor
5	DT/SD	Dead Time Set Resistor
6	6 GND Signal Ground	
7	PGND	Power Ground
8	OUT	High-Side Floating Supply Return

#### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A=25^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Min.	Тур.	Max.	Unit
VB	High-Side Floating Supply	-0.3		465.0	V
V <sub>OUT</sub>	High-Side Floating Supply Return	-0.3		440.0	V
V <sub>RCT</sub>	RCT Pins Input Voltage		$V_{DD}$		V
I <sub>CL</sub>	Clamping Current Level <sup>(1)</sup>			25	mA
dV <sub>OUT</sub> /dt	Allowable Offset Voltage Slew Rate		50		V/ns
T <sub>A</sub>	Operating Temperature Range	-40		+125	°C
T <sub>STG</sub>	Storage Temperature Range	-65		+150	°C
P <sub>D</sub>	Power Dissipation		2.1		W
$\Theta_{\sf JA}$	Thermal Resistance (Junction-to-Air)		70		°C/W

#### Note:

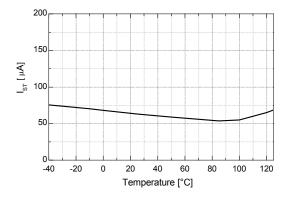
 Do not supply a low-impedance voltage source to the internal clamping Zener diode between the GND and the VDD pin of this device.

#### **Electrical Characteristics**

 $V_{BIAS}\,(V_{DD},\,V_{B}\,\text{-}V_{OUT})\text{=}14.0V,\,T_{A}\text{=}25^{\circ}\text{C},\,\text{unless otherwise specified}.$ 

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
High Vol	age Supply Section						
$V_{DC}$	High Voltage Supply Voltage		440			V	
Low-Side	Supply Characteristics (V <sub>DD</sub> )						
VDD <sub>UV+</sub>	V <sub>DD</sub> UVLO Positive-Going Threshold	V <sub>DD</sub> Increasing	9	11	13		
VDD <sub>UV-</sub>	V <sub>DD</sub> UVLO Negative-Going Threshold	V <sub>DD</sub> Decreasing	7.8	8.8	9.8	V	
VDD <sub>UHY</sub>	V <sub>DD</sub> -Side UVLO Hysteresis			2.2			
V <sub>CL</sub>	Supply Camping Voltage	I <sub>DD</sub> =10mA	14.4	15.4			
I <sub>ST</sub>	Startup Supply Current	V <sub>DD</sub> =9V		60	90		
$I_{QDD}$	Low-Side Quiescent Supply Current	$R_{DT}$ =100k $\Omega$		230	380	μA	
I <sub>DD</sub>	Dynamic Operating Supply Current	20kHz, C <sub>L</sub> =1nF		0.6		mA	
High-Sid	e Supply Characteristics (VB-V <sub>OUT</sub> )			1		U.	
V <sub>HSUV+</sub>	High-Side UVLO Positive-Going Threshold	V <sub>B</sub> -V <sub>OUT</sub> Increasing	8	9	10		
V <sub>HSUV</sub> -	High-Side UVLO Negative-Going Threshold	V <sub>B</sub> -V <sub>OUT</sub> Decreasing	7.5	8.5	9.5	V	
V <sub>HSUHY</sub>	V <sub>BS</sub> Supply UVLO Hysteresis			0.5		1	
I <sub>QHS</sub>	High-Side Quiescent Supply Current		7	50	90	μΑ	
I <sub>PBS</sub>	High-Side Dynamic Operating Supply Current	20kHz, C <sub>L</sub> =1nF		130	180		
Oscillato	r Characteristics						
f <sub>osc</sub>	Oscillation Frequency	$R_T$ =50k $\Omega$ , $C_T$ =330pF	18	20	22	kHz	
D	Duty Cycle	Running Mode	47.5	49.0		%	
V <sub>RCT+</sub>	Upper Threshold Voltage of RCT	Running Mode		$V_{DD}$			
V <sub>RCT</sub> -	Lower Threshold Voltage of RCT	Running Mode		V <sub>DD</sub> /4			
$V_{IH}$	Logic "1" Input Voltage of RCT	Running Mode		3/4 V <sub>DD</sub>		V	
$V_{IL}$	Logic "0" Input Voltage of RCT	Running Mode		/-	3/5 V <sub>DD</sub>		
t <sub>D</sub>	Dead Time	$R_{DT}$ =100k $\Omega$	440	540	640		
t <sub>DMIN</sub>	Minimum Dead Time	$V_{DT/\overline{SD}}=V_{DD}$	280	400	520	ns	
Protectio	n Characteristics				7	u.	
V <sub>SD+</sub>	Shutdown "1" Input Voltage		2.5			.,	
V <sub>SD-</sub>	Shutdown "0" Input Voltage	V <sub>SD/DT</sub> =0 After Run			1	V	
I <sub>SD</sub>	Shutdown Current	Mode			350	μA	
t <sub>SD</sub>	Shutdown Propagation Delay			180		Ns	
Internal N	MOSFET Section				7	7	
I <sub>LKMOS</sub>	Internal MOSFET Leakage Current	V <sub>DS</sub> =400V			50	μA	
Ron	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =190mA		4.6	6.0	Ω	
Is	Maximum Continuous Drain-Source Diode Forward Current	33 1 , 15 12 13 11		0.38		A	
I <sub>SM</sub>	Maximum Pulsed Continuous Drain-Source Diode Forward Current			3.04		Α	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =0.38A			1.2	V	

### **Typical Performance Characteristics**



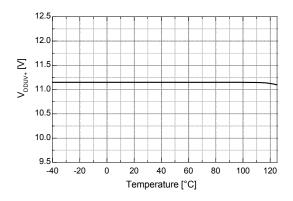


Figure 5. Startup Current vs. Temperature

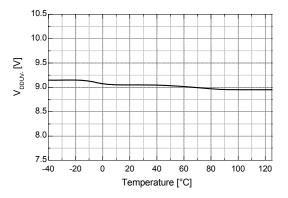


Figure 6. V<sub>DD</sub> UVLO+ vs. Temperature

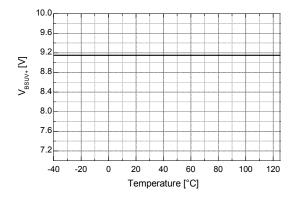


Figure 7.  $V_{DD}$  UVLO- vs. Temperature

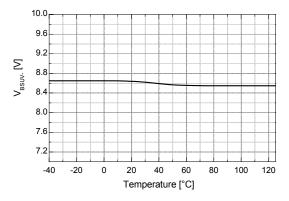


Figure 8. VB.V<sub>OUT</sub> UVLO+ vs. Temperature

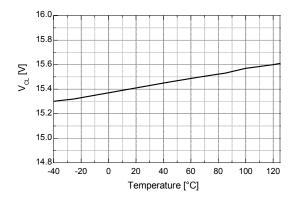
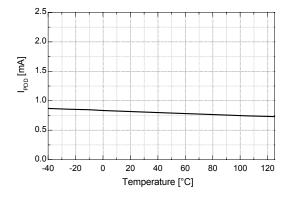


Figure 9.  $VB.V_{OUT}$  UVLO- vs. Temperature

Figure 10. V<sub>CL</sub> vs. Temperature

### **Typical Performance Characteristics** (Continued)

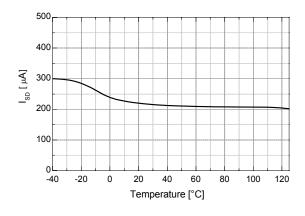


400 300 100 40 -20 0 20 40 60 80 100 120 Temperature [°C]

500

Figure 11. I<sub>PDD</sub> vs. Temperature

Figure 12. I<sub>QDD</sub> vs. Temperature



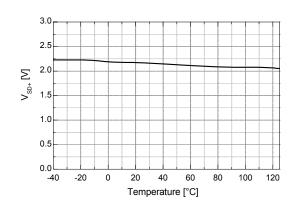
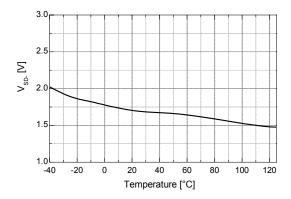


Figure 13. I<sub>SD</sub> vs. Temperature

Figure 14. V<sub>SD</sub>+ vs. Temperature



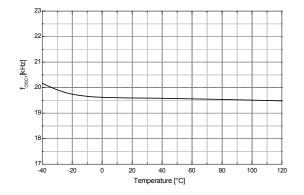


Figure 15. V<sub>SD</sub>- vs. Temperature

Figure 16. Operating Frequency vs. Temperature

### **Typical Performance Characteristics** (Continued)

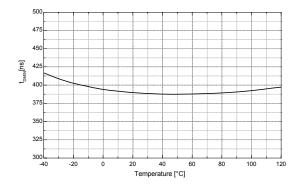


Figure 17. t<sub>DMIN</sub> vs. Temperature

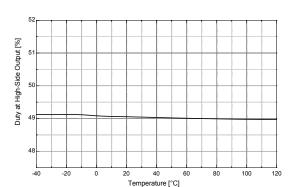


Figure 19. High-Side Duty Ratio vs. Temperature

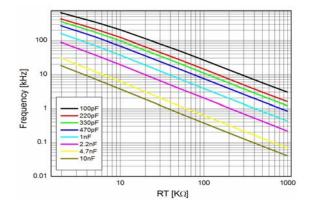


Figure 21. Frequency vs. R<sub>T</sub>

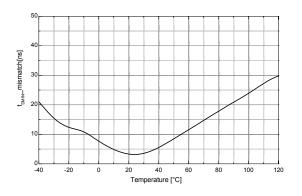


Figure 18. Dead-Time Mismatch vs. Temperature

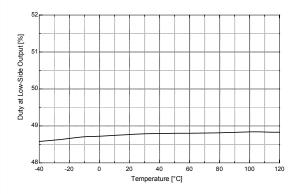


Figure 20. Low-Side Duty Ratio vs. Temperature

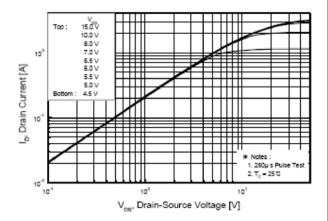


Figure 22. On-Region Characteristics

#### **Typical Performance Characteristics** (Continued)

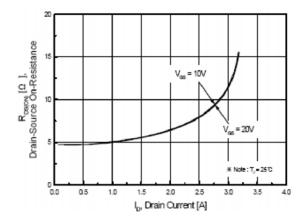


Figure 23. On-Resistance Variation vs.
Drain Current and Gate Voltage

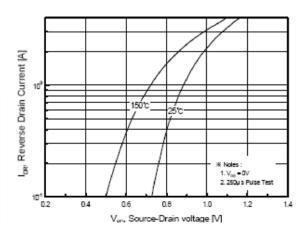


Figure 24. Body Diode Forward Voltage Variation vs.
Source Current and Temperature

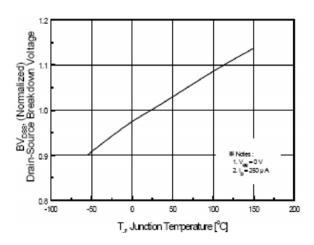


Figure 25. Breakdown Voltage Variation vs. Temperature

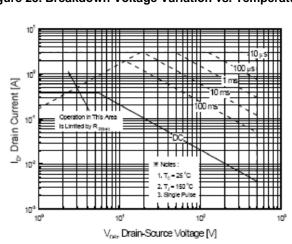


Figure 27. Maximum Safe Operating Area



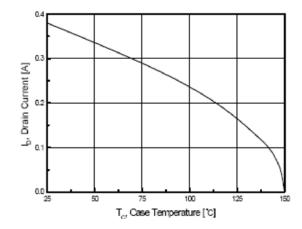


Figure 28. Maximum Drain-Current vs. Case Temperature

#### **Application Information**

#### 1. Under-Voltage Lockout (UVLO) Function

FAN7387V has a UVLO circuit for a low-side and high-side block. When  $V_{\text{DD}}$  reaches to the VDDUV+, the UVLO circuit is released and the FAN7387V operates normally. At UVLO condition, the FAN7387V has a low supply current of less than 130µA. Once UVLO is released, FAN7387V operates normally until  $V_{\text{DD}}$  goes below VDDUV-, the UVLO hysteresis. FAN7387V also has a high-side gate driver. The supply for the high-side driver is applied between VB and  $V_{\text{OUT}}$ . To prevent malfunction at low supply voltage between VB and  $V_{\text{OUT}}$ , FAN7387V provides an additional UVLO circuit. If VB-V\_{\text{OUT}} is under  $V_{\text{HSUV}^+}$ , the driver holds LOW state to turn off the high-side switch. Once the voltage of VB-V\_{\text{OUT}} is higher than  $V_{\text{HSUV}^+}$ , after VB-V\_{\text{OUT}} exceeds  $V_{\text{HSUV}^-}$ , the operation of driver resumes.

#### 2. Oscillator

The running frequency is determined by an external timing resistor ( $R_T$ ) and timing capacitor ( $C_T$ ). The charge time of capacitor  $C_T$  from 1/4  $V_{DD}$  to  $V_{DD}$  determines the running frequency of gate driver output ( $V_{OUT}$ ).

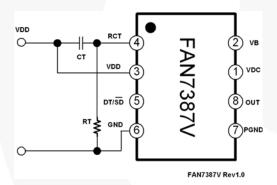


Figure 29. Typical Connection Method

Figure 30 shows the typical waveforms of RCT and internal signals (LO and HO) of IC. From the circuit analysis, the discharging time of RCT, t, is given by:

$$V_{RCT}(t) = V_{DD} \times In \left( \frac{-t}{R_T \cdot C_T} \right)$$
 (1)

From Equation 1, it is possible to calculate the discharging time, t, from  $V_{DD}$  to one quarter (1/4) of  $V_{DD}$  by substituting  $V_{RCT(t)}$  with 1/4  $V_{DD}$ .

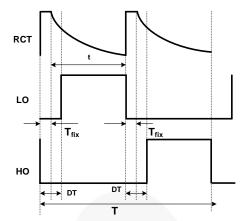


Figure 30. Typical Waveforms of RCT and Internal Signal (LO, HO) of IC

$$t = 1.38 \bullet R_T \bullet C_T \tag{2}$$

The running frequency of IC is determined by 1/t and is approximately given as:

$$f_{\text{running}} = \frac{1}{t} = \frac{1}{2(t + t_{\text{fix}})}$$
 (3)

where t is the discharging time of the RCT voltage and  $t_{\text{fix}}$  is constant value about 450ns of IC.

## 3. Programming Dead Time Control / Shutdown

A multi-function pin controls dead time using an external resistor ( $R_{DT}$ ) and protects abnormal condition using an external switch. This pin should be connected to an external capacitor to maintain stable operation.

If the voltage of DT/SD is decreased to under 1V by an external switch, such as the TR or MOSFET, the FAN7387V enters shutdown mode. In this mode, the FAN7387V doesn't have any output signal.

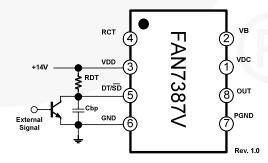
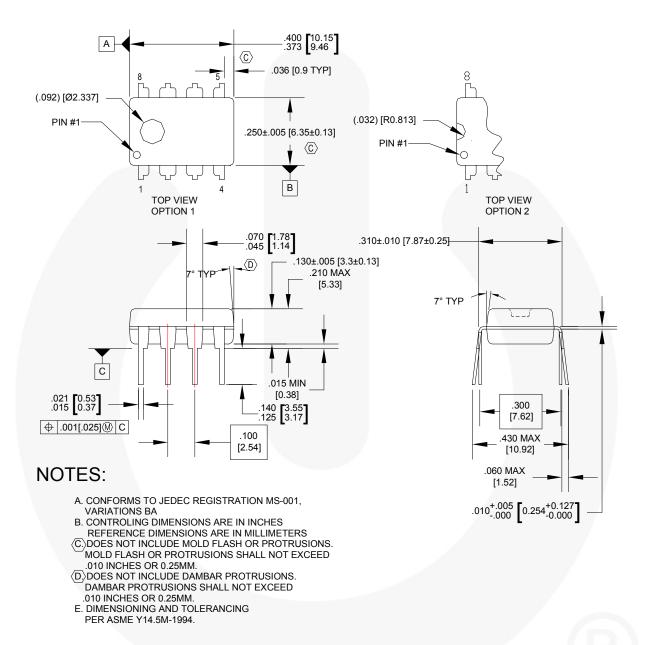


Figure 31. External Shutdown Circuit

#### **Physical Dimensions**



#### N08EREVG

#### Figure 32. 8-Lead Dual Inline Package (DIP)

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